

Amendments to the Claims

Claims 1-26 (Cancelled).

E' 27. (Currently amended) A gate stack, comprising:
a gate oxide polysilicon layer over a semiconductive substrate;
a gate oxide polysilicon layer on the gate oxide polysilicon layer;
a metal silicide layer on the polysilicon gate oxide layer;
a layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$ formed over and in physical contact with the metal silicide, wherein x is from 0.39 to 0.65, y is from 0.02 to 0.56, and z is from 0.05 to 0.33; the metal silicide being the product of a process in which the metal silicide is subjected to an anneal treatment after the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$ is formed; and
a silicon nitride layer on the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$, the polysilicon layer, the gate oxide layer, the metal silicide layer, the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$, and the silicon nitride layer being patterned to form the gate stack.

Claims 28-32 (Cancelled).

33. (Previously presented) The gate stack of Claim 27, where the layer comprising $\text{Si}_x\text{N}_y\text{O}_z\text{:H}$ has a thickness of from about 250Å to about 650Å.

Claims 34-35 (Cancelled).

36. (Previously presented) The gate stack of claim 27 wherein y is from 0.02 to less than 0.1.

37. (Previously presented) The gate stack of claim 27 wherein $x=0.5$, $y=0.37$ and $z=0.13$.

38. (Previously presented) The gate stack of claim 27 wherein the metal silicide layer comprises titanium.

39. (New) A gate stack comprising:
a polysilicon layer over a semiconductive substrate;
a metal-comprising layer over the polysilicon layer;
an antireflective material on the metal comprising layer, the antireflective material comprising carbon, nitrogen, silicon, oxygen and hydrogen; and
a silicon nitride layer on the antireflective material.

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40. (New) The gate stack of claim 39 wherein the antireflective material comprises greater than about 1% carbon, by weight.

41. (New) The gate stack of claim 39 wherein the antireflective material comprises $\text{Si}_x\text{N}_y\text{O}_z\text{H}$, where x is from 0.39 to 0.65, y is from 0.02 to 0.56, and z is from 0.05 to 0.33.

42. (New) The gate stack of claim 39 wherein the metal-comprising layer is a metal silicide layer.

43. (New) The gate stack of claim 39 wherein the metal-comprising layer comprises at least one of tungsten and titanium.
